

b) Amendments to the Claims

Please cancel claims 8 and 9 without prejudice or disclaimer. A detailed listing of all the claims that are or were in the application is provided.

--1. (Previously Presented) A sputtering method for forming a film on a substrate in a film forming space while monitoring emission intensity of plasma, the method comprising the steps of:

detecting a thickness of the film formed on said substrate;
comparing a detected value with a preset value of the film thickness;
deciding a target value of the emission intensity that will provide the preset value of the film thickness in accordance with a compared result; and
adjusting the emission intensity to the target value to increase a transmittance of the film formed on the substrate to compensate for an increase in resistance of the film.

2. (Previously Presented) The sputtering method according to claim 1, further comprising controlling a flow rate of at least one gas introduced into said film forming space, thereby adjusting the intensity to the target value of the emission intensity.

3. (Previously Presented) The sputtering method according to Claim 1, wherein a target containing In is employed as a sputtering target.

4. (Previously Presented) The sputtering method according to Claim 1, wherein a cylindrical rotating target is employed as a sputtering target.

5. (Previously Presented) The sputtering method according to Claim 2, wherein oxygen gas is selected as the gas for which the flow rate is controlled.

6. (Previously Presented) The sputtering method according to Claim 1, wherein the target value of the emission intensity is set to fall in a predetermined range defined beforehand.

7. (Previously Presented) The sputtering method according to Claim 6, wherein if the target value deviates from said predetermined range, sputtering is stopped.

Claims 8. and 9. (Cancelled)